

To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SH26

Silicon N Channel IGBT High Speed Power Switching

RENESAS

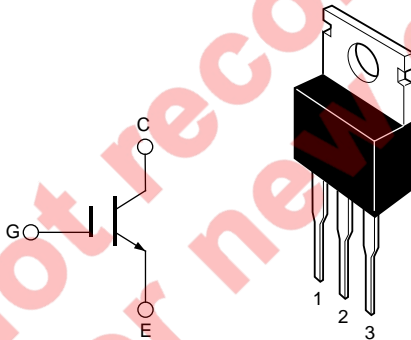
ADE-208-788A(Z)
2nd. Edition
May 1999

Features

- High speed switching
- Low on-voltage

Outline

TO-220AB



1. Gate
2. Collector (Flange)
3. Emitter

Absolute Maximum Ratings (Ta = 25°C)

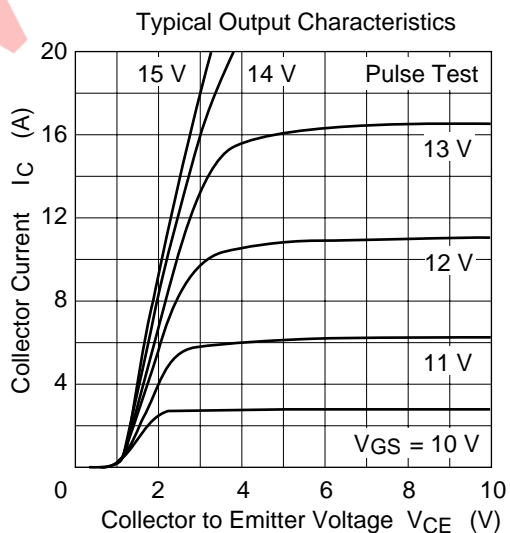
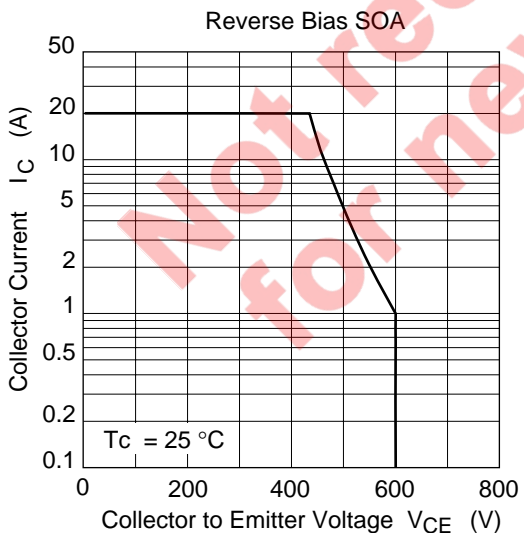
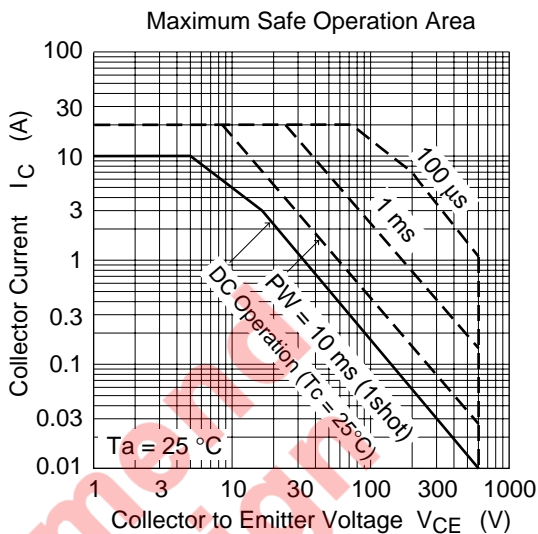
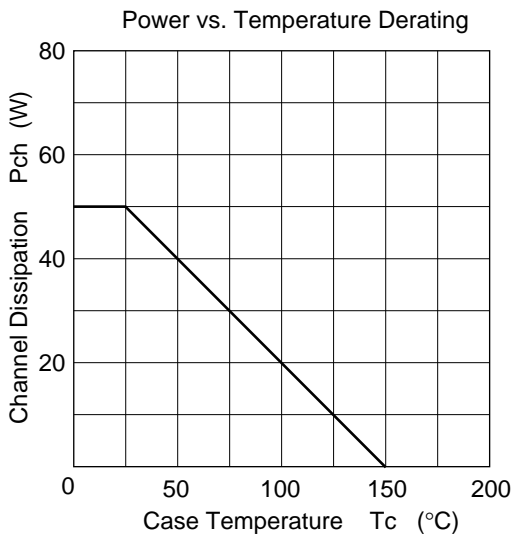
Item	Symbol	Ratings	Unit
Collector to Emitter voltage	V_{CES}	600	V
Gate to Emitter voltage	V_{GES}	±20	V
Collector current	I_C	10	A
Collector peak current	$i_c(\text{peak})$	20	A
Collector dissipation	P_C ^{Note1}	50	W
Channel temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

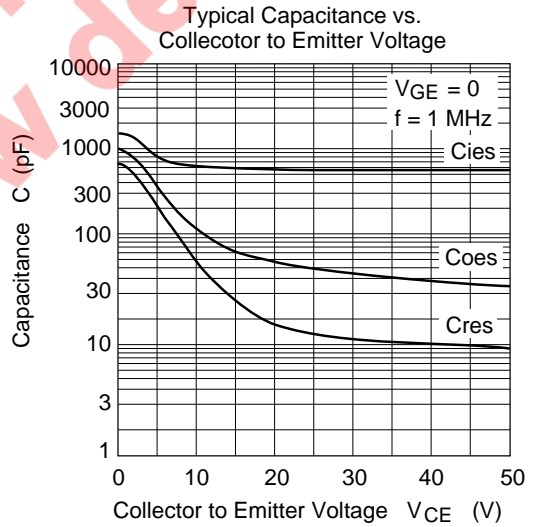
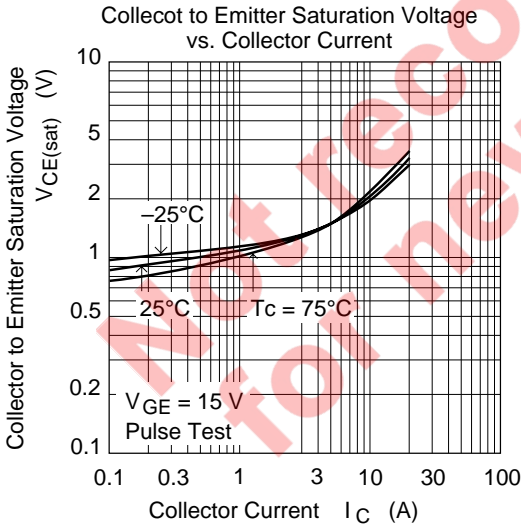
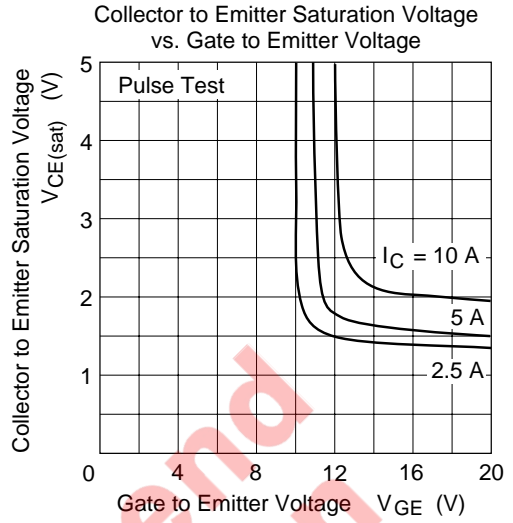
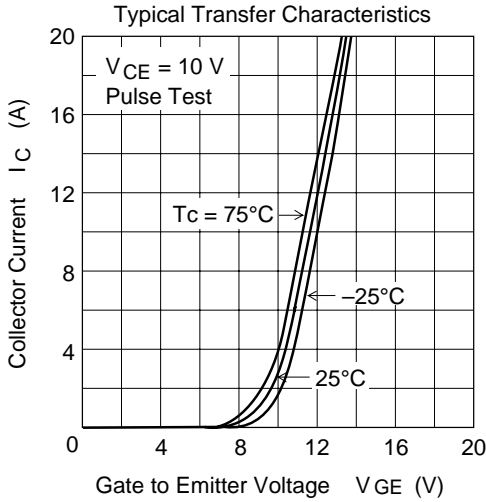
Note: 1. Value at $T_c = 25^\circ\text{C}$

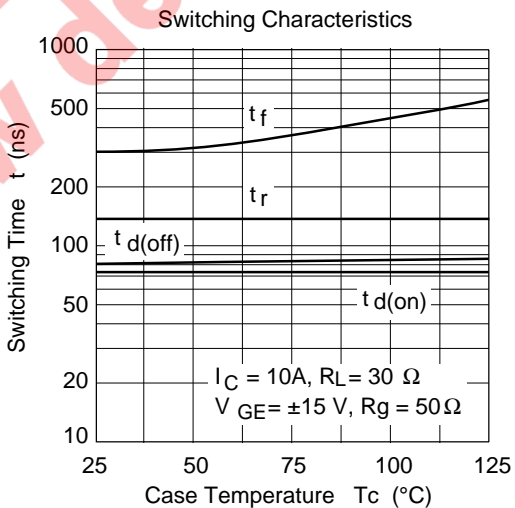
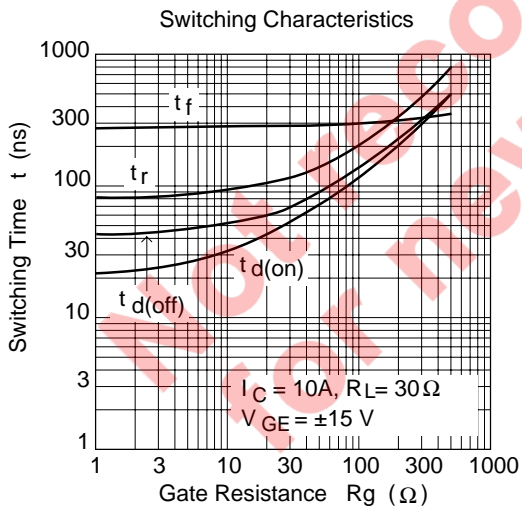
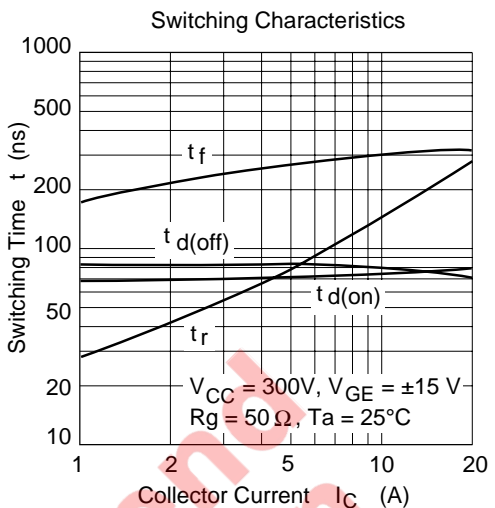
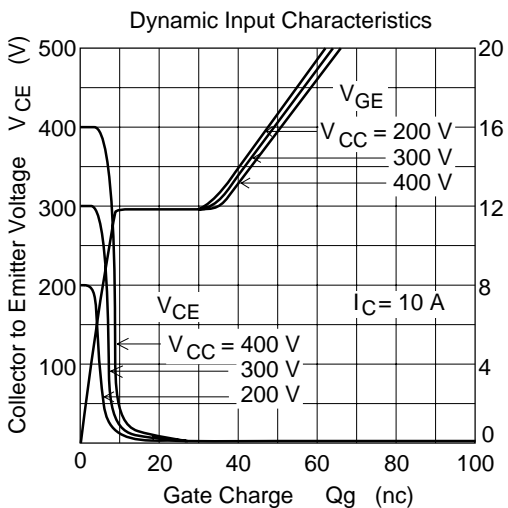
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Zero gate voltage collector current	I_{CES}	—	—	100	μA	$V_{CE} = 600\text{V}, V_{GE} = 0$
Gate to emitter leak current	I_{GES}	—	—	±1	μA	$V_{GE} = \pm 20\text{V}, V_{CE} = 0$
Gate to emitter cutoff voltage	$V_{GE(\text{off})}$	6.0	—	8.0	V	$I_C = 10\text{mA}, V_{CE} = 10\text{V}$
Collector to emitter saturation voltage	$V_{CE(\text{sat})}$	—	2.1	2.6	V	$I_C = 10\text{A}, V_{GE} = 15\text{V}$
Input capacitance	C_{ies}	—	620	—	pF	$V_{CE} = 10\text{V}, V_{GE} = 0$ $f = 1\text{MHz}$
Switching time	t_r	—	140	—	ns	$I_C = 10\text{A}$
	t_{on}	—	215	—	ns	$R_L = 30\ \Omega$
	t_f	—	300	600	ns	$V_{GS} = \pm 15\text{V}$
	t_{off}	—	380	760	ns	$R_g = 50\ \Omega$

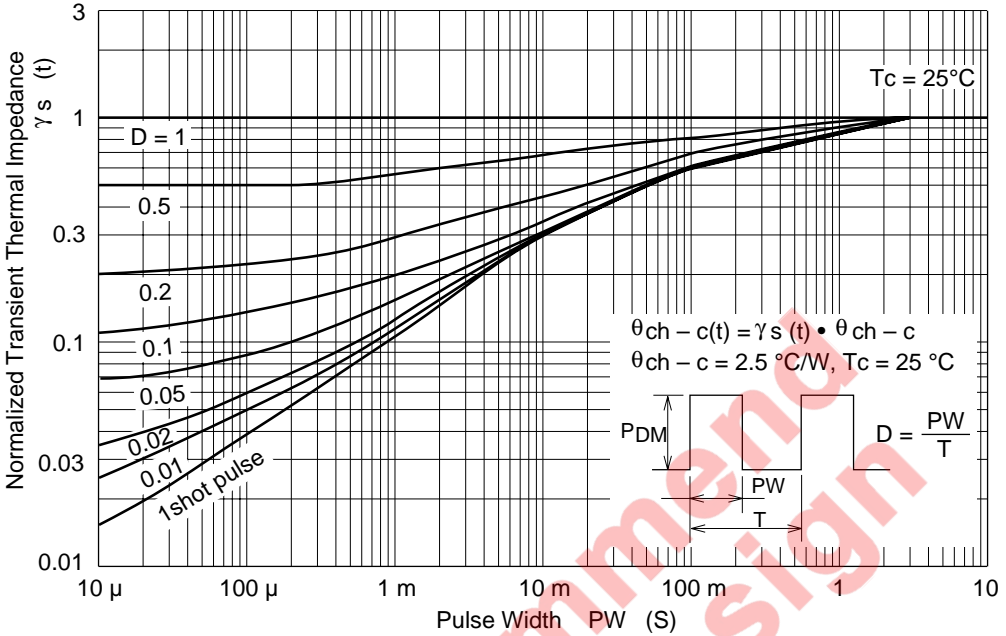
Main Characteristics



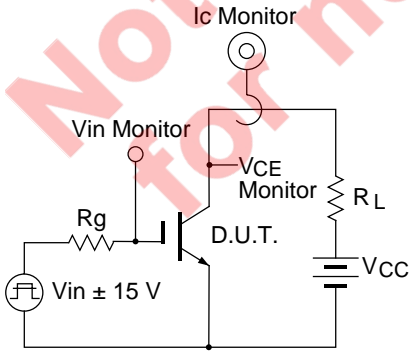




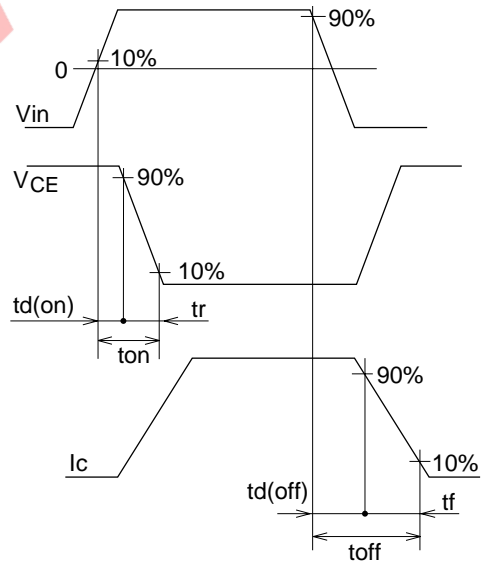
Normalized Transient Thermal Impedance vs. Pulse Width



Switching Time Test Circuit

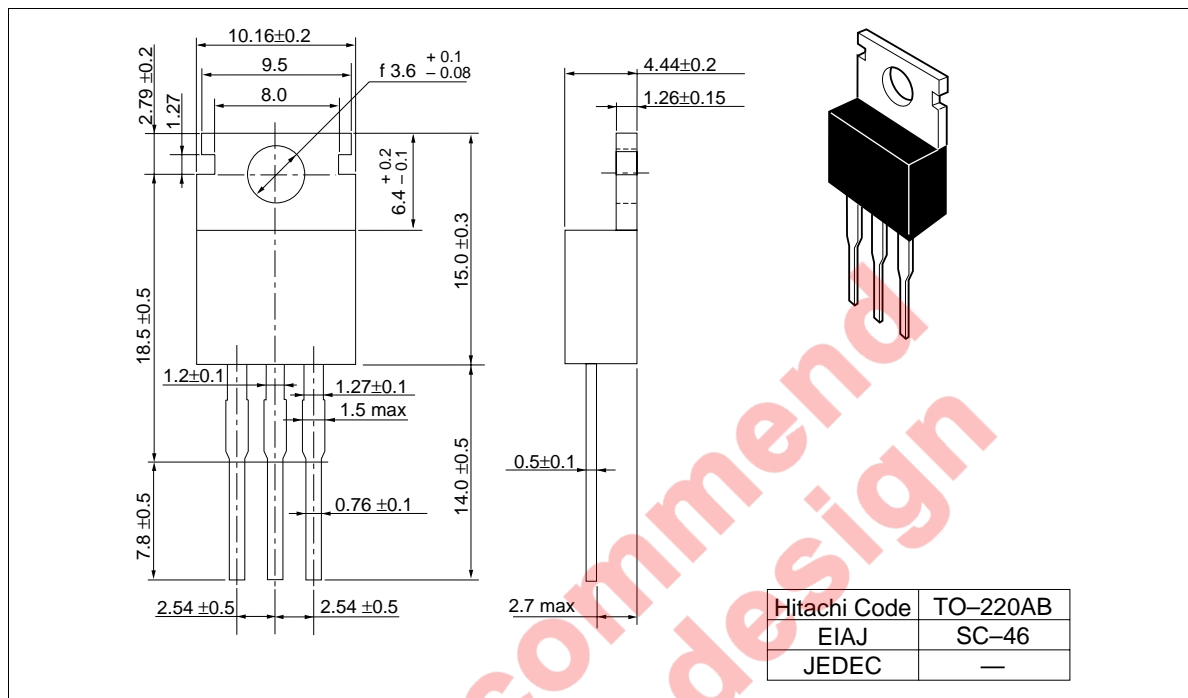


Waveform



Package Dimensions

Unit: mm



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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL NorthAmerica : <http://semiconductor.hitachi.com/>
 Europe : <http://www.hitachi-eu.com/hel/ecg>
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1>(408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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